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(54) Title of the Invention: Multi-wavelength semiconductor laser device
Abstract Title: Multi-wavelength semiconductor laser device

(57) A multi-wavelength semiconductor laser device comprises a block 103 and a plurality of laser diodes 111 producing light at emission wavelengths that are different from each other, wherein the block includes a "V"-shape cross-section groove 205 with two side faces 209 and the laser diodes emit their laser beams in the same direction. Alternatively, the laser diodes 111 are mounted on the side faces (109, Figure 1) and bottom face (107, Figure 1) of a groove (105, Figure 1) having a rectangular cross-section so that each laser diode emits light in a predetermined direction. The block may be mounted on a stem 101 and also comprise a projection 403 having first and second side faces 405 the first and second flat faces 401. The laser diodes may be mounted on two faces or more among the faces of the first and second side and flat faces.

FIG. 3

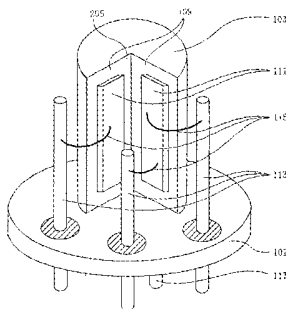
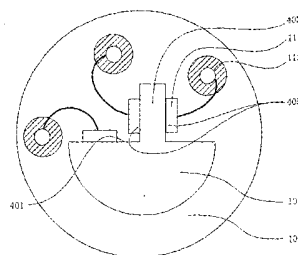


FIG. 7



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DRAWINGS

FIG. 1

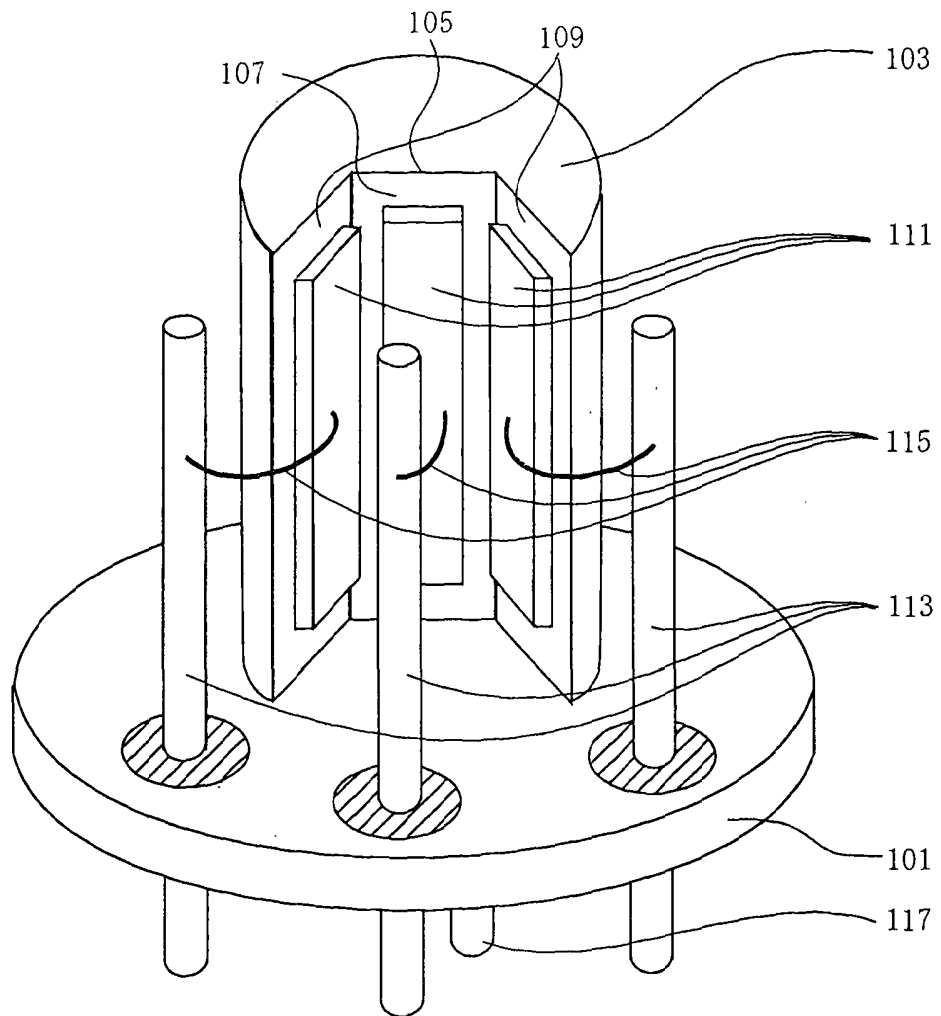


FIG. 2

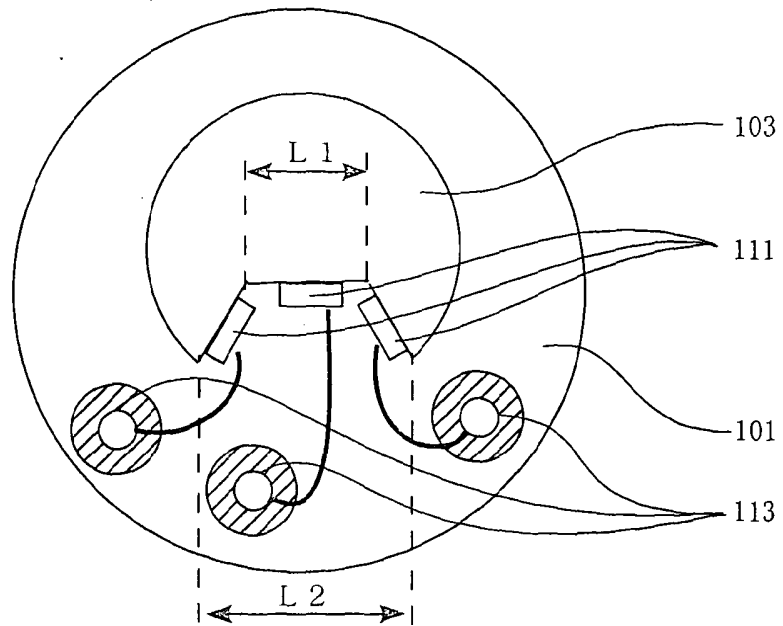


FIG. 3

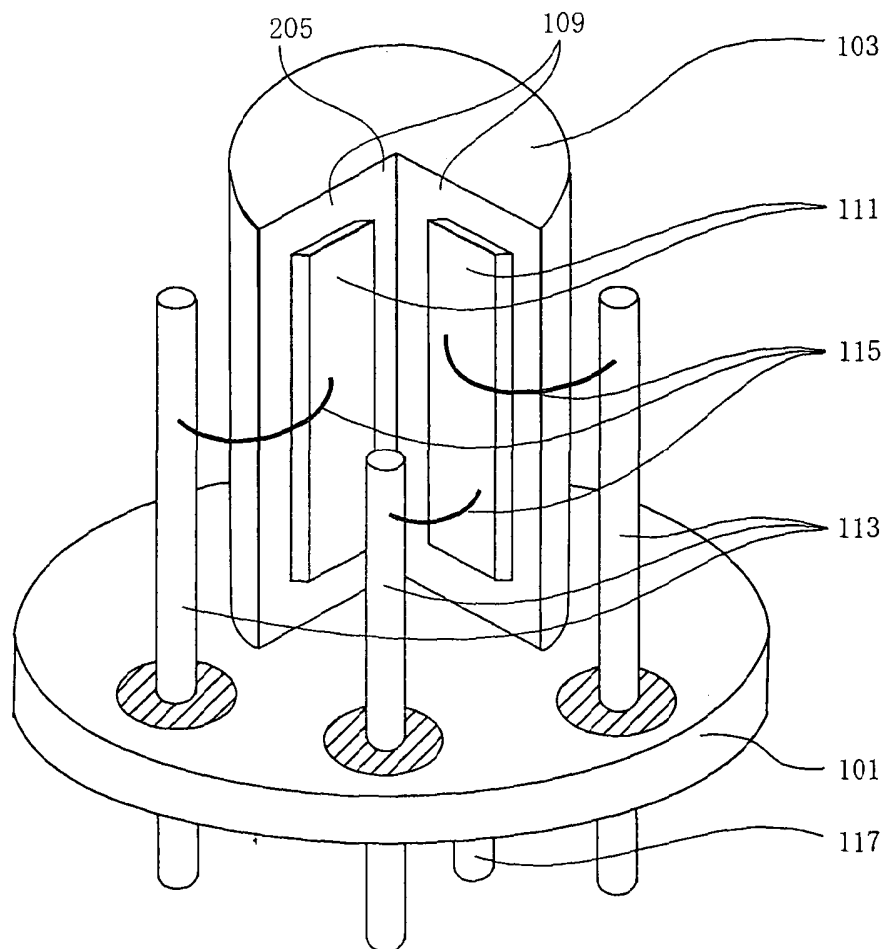


FIG. 4

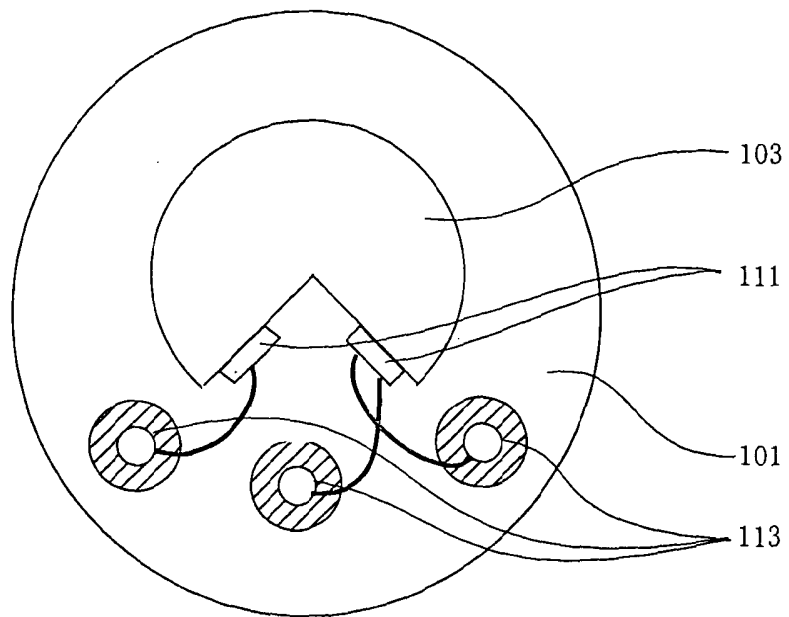


FIG. 5

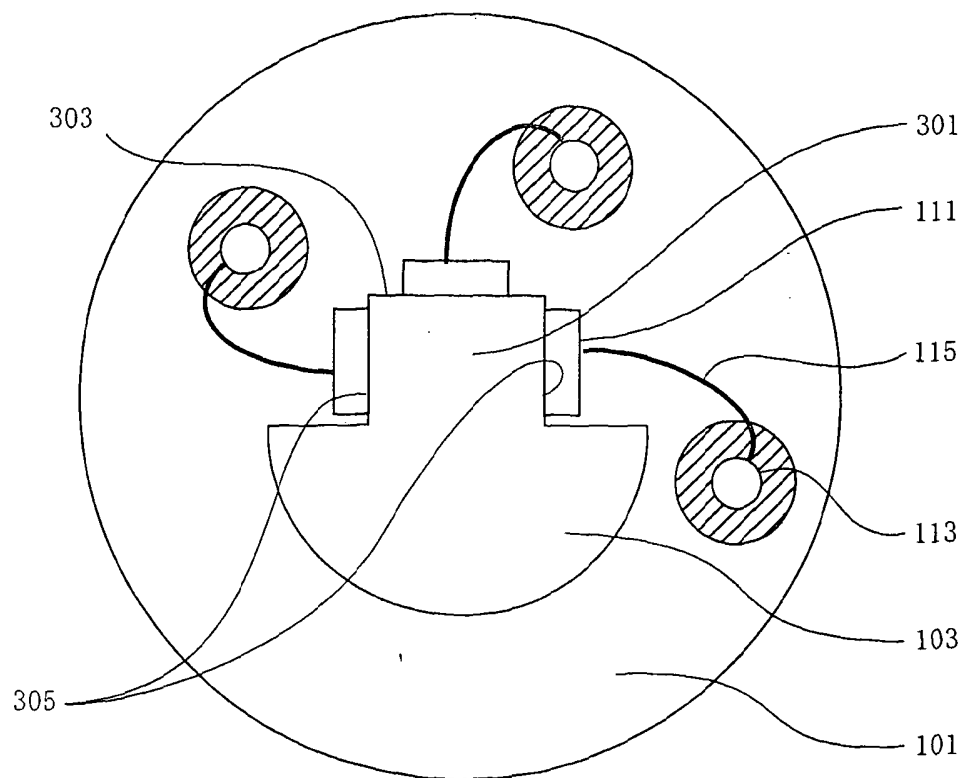


FIG. 6

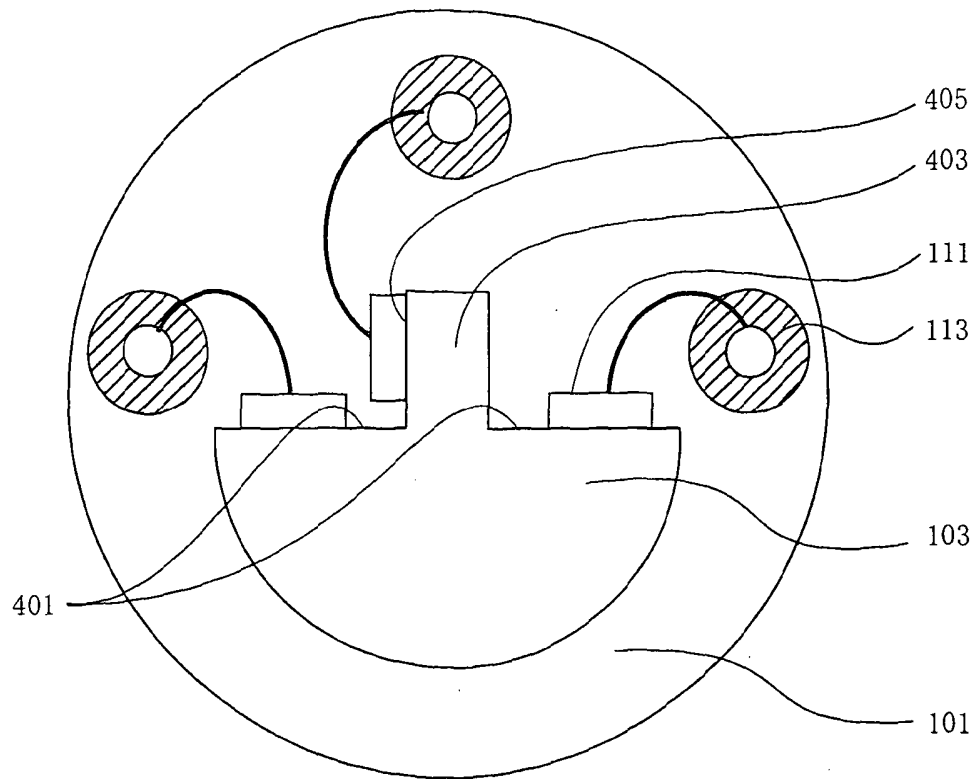
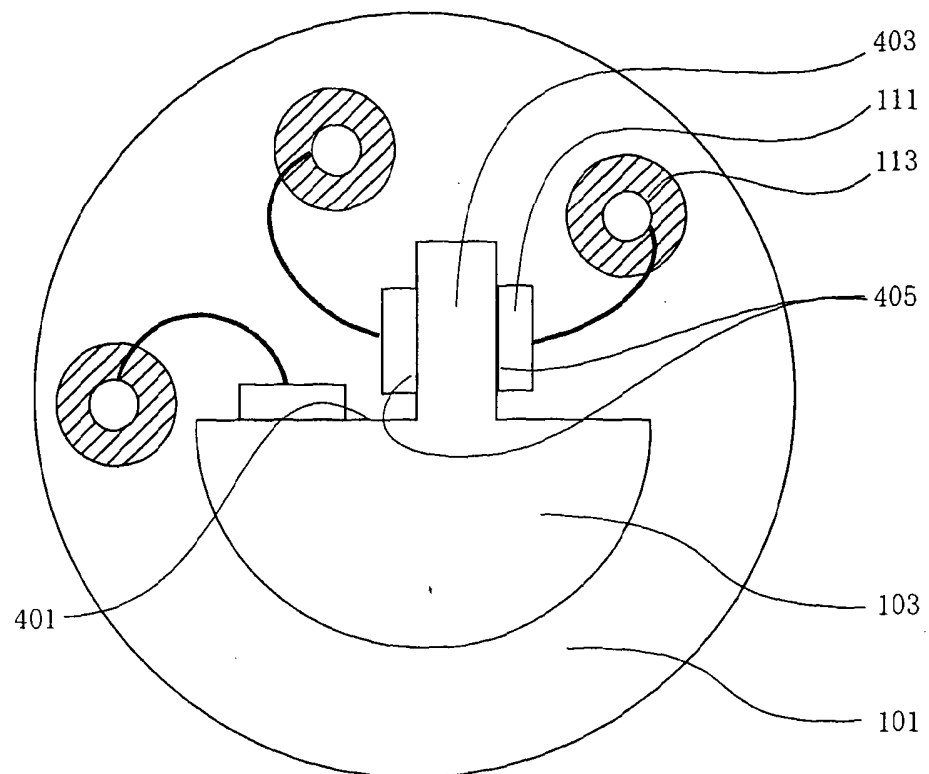


FIG. 7



SPECIFICATION

Multi-Wavelength Semiconductor Laser Device

Field of the Invention

[0001]

The present invention relates to a multi-wavelength semiconductor laser device that has a plurality of laser diodes for emitting different wavelength light beams.

Background Art

[0002]

An optical disc such as a compact disc (CD), a digital versatile disc (DVD), and a "Blu-ray Disc" TM (BD) has been increasingly used now as large capacity storage media. Laser diodes used for reading/writing from/to these discs have respective different emission wavelengths: a CD laser diode has an emission wavelength of 780 nm band (infrared), a DVD laser diode has an emission wavelength of 650 nm band (red), and a BD laser diode has an emission wavelength of 405 nm band (blue-violet). Hence, in order to treat data for a CD, a DVD, and a BD in a single optical disc drive, required are three light sources of infrared, red, and blue-violet.

[0003]

In a case of configuring a multi-wavelength semiconductor laser device such that different wavelength laser-diode chips are arranged side by side, their emission points are spaced largely apart from each other, resulting in difficulty in optical design. For dealing therewith, there has been a conventional multi-wavelength semiconductor laser device, in which red and infrared laser diodes are arranged in parallel and bonded on a blue-violet laser diode that is mounted on a heat sink, to be able to treat data for CD, DVD, and BD in a single optical disc drive (see, for example, JP 2006-59471A).

[0004]

In the multi-wavelength semiconductor laser device described in JP 2006-59471A, however, since the infrared and the red laser diodes are bonded on the blue-violet laser diode, there has been a problem in that heat generated during operation of the infrared and the red laser diodes cannot efficiently dissipate to the heat sink. Moreover, this configuration makes their assembly process complicated, resulting in a problem of high manufacturing costs.

Summary of the Invention

[0005]

The present invention is made to resolve such problems as mentioned above, and provides a multi-wavelength semiconductor laser device that has closely arranged laser-diode chips' emission

points, and is easy in optical design and excellent in heat dissipation, as well as being easily manufactured.

[0006]

A multi-wavelength semiconductor laser device according to a first aspect of the invention includes a block and a plurality of laser diodes whose emission wavelengths are different from each other, wherein the block is formed having a rectangular cross-section groove with a bottom face and two side faces extending in a predetermined direction, and the laser diodes are mounted on the bottom face and the side faces of the groove so that their laser beams emit in the predetermined direction.

[0007]

A multi-wavelength semiconductor laser device according to a second aspect of the invention includes a block and a plurality of laser diodes whose emission wavelengths are different from each other, wherein the block is formed having a "V"-shape cross-section groove with two side faces extending in a predetermined direction, and the laser diodes are mounted on both side faces of the groove so that their laser beams emit in the predetermined direction.

[0008]

A multi-wavelength semiconductor laser device according to a third aspect of the invention includes a block and a plurality of

laser diodes whose emission wavelengths are different from each other, wherein the block is formed having a rectangular projection, and the laser diodes are mounted on a top face and side faces of the projection.

[0009]

A multi-wavelength semiconductor laser device according to a fourth aspect of the invention includes a block and a plurality of laser diodes whose emission wavelengths are different from each other, wherein the block is formed having a flat face and a projection extending from the flat face, and the laser diodes are mounted on the flat face of the block and side faces of the projection.

[0010]

According to the invention, a multi-wavelength semiconductor laser device can be realized that has closely arranged laser-diode chips' emission points, and is easy in optical design and excellent in heat dissipation, as well as being easily manufactured.

Brief Description of the Drawings

[0011]

FIG. 1 is a schematic oblique perspective view of a configuration of a multi-wavelength semiconductor laser device according to Embodiment 1 of the present invention;

FIG. 2 is a schematic plan view of the configuration of the multi-wavelength semiconductor laser device of Embodiment 1;

FIG. 3 is a schematic oblique perspective view of a configuration of a multi-wavelength semiconductor laser device according to Embodiment 2 of the invention;

FIG. 4 is a schematic plan view of the configuration of the multi-wavelength semiconductor laser device of Embodiment 2;

FIG. 5 is a schematic plan view of a configuration of a multi-wavelength semiconductor laser device according to Embodiment 3 of the invention;

FIG. 6 is a schematic plan view of a configuration of a multi-wavelength semiconductor laser device according to Embodiment 4 of the invention; and

FIG. 7 is a schematic plan view of a configuration of a multi-wavelength semiconductor laser device according to Embodiment 5 of the invention.

Description of the Preferred Embodiments

[0012]

Embodiment 1

FIG. 1 illustrates an oblique perspective view of a multi-wavelength semiconductor laser device according to Embodiment 1, and FIG. 2 illustrates its plan view. The multi-wavelength semiconductor laser device of this embodiment includes a stem 101 that is formed from a metal plate into a discoid shape; a cylindrical block 103 whose bottom face is placed on the top face of the stem 101; three laser diodes 111 that are mounted on a bottom face 107 and side faces 109 of a rectangular cross-section groove 105 formed laterally in the block 103; lead pins 113 that penetrate the stem 101; bonding wires 115 that connect the laser diodes 111 with the lead pins 113, respectively; and a ground pin 117 that is joined to the stem 101.

[0013]

The block 103 is formed of a metal material having high thermal conductivity, such as a copper alloy, and the groove 105 formed laterally in the block 103 coincides in direction with emission directions (resonant directions) of the laser diodes 111 mounted on the bottom face 107 and the side faces 109 of the groove 105. The groove 105 in this embodiment expands in cross section toward its opening, i.e., the outermost width $L2$ of the opening is

wider than the width LI of the bottom face, thereby more facilitating die bonding and wire bonding of the laser diodes 111.

[0014]

The three laser diodes 111 are respectively soldered to the bottom face 107 and the side faces 109 of the groove 105 formed in the block 103. Additionally, the laser diodes 111 may be mounted on these faces 107, 109 with submounts interposed therebetween. The laser diodes 111 are aligned so that their laser beams emit in parallel to the direction of the groove 105. Note that emission wavelengths of the three laser diodes 111 are a 780 nm band (infrared), a 650 nm band (red), and a 405 nm band (blue-violet), and there is no restriction on their mounting order.

[0015]

The lead pins 113 are penetrated through the stem 101 with insulators each interposed therebetween and arranged near the respective laser diodes 111 mounted on the groove 105 of the block 103. Electrical connections are respectively made by the bonding wires 115 across the lead pins 113 and the p-side electrodes (not shown) of the laser diodes 111.

[0016]

The ground pin 117 is welded to the stem 101 and electrically connected to the n-side electrodes (not shown) of the laser diodes

111 through the stem 101 and the block 103.

[0017]

With the multi-wavelength semiconductor laser device thus configured, since the three laser diodes 111 are soldered to the block 103 directly or with submounts interposed therebetween, heat generated during operation of the laser diodes 111 can efficiently dissipate externally through the block 103.

[0018]

Moreover, since the lead pins 113 are arranged near the respective laser diodes 111 mounted on the groove 105 of the block 103, wire bonding is facilitated across the lead pins 113 and the laser diodes 111, making easier the assembly process of the multi-wavelength semiconductor laser device compared to prior arts and thus reducing its manufacturing costs.

[0019]

While, in this embodiment, the groove 105 formed in the block 103 has a shape such that its cross section expands toward the groove opening, the present invention is not limited to such a shape but may employ a groove 105 that has parallel side faces 109 opposite to each other, i.e., the widths $L1$ and $L2$ shown in FIG. 2 may have a relation of $L1 = L2$, what is more, $L1 > L2$. In particular, by forming a groove 105 in such a shape, as in this

embodiment, that its cross section expands toward the groove opening ($L1 < L2$), die bonding and wire bonding of the laser diodes 111 can be more easily performed.

[0020]

Moreover, while the block 103 in this embodiment has a cylindrical shape with the groove 105 formed therein, the present invention is not limited to such a shape but may employ a block that has a cross section of a polygonal prism shape with such a groove formed therein.

[0021]

Furthermore, while the block 103 formed separately from the stem 101 is placed thereon in this embodiment, the stem 101 and the block 103 may be formed in one piece by, for example, metal molding.

[0022]

According to this embodiment, a multi-wavelength semiconductor laser device includes a block 103 and laser diodes 111 whose emission wavelengths are different from each other, wherein the block 103 has a rectangular cross-section groove 105 extending in a predetermined direction having a bottom face 107 and two side faces 109, and the laser diodes 111 are mounted on these faces 107, 109 so that their laser beams emit in the

predetermined direction. Therefore, a multi-wavelength semiconductor laser device can be realized that has closely arranged emission points of the laser diodes 111, and is easy in optical design and excellent in heat dissipation, as well as being easily manufactured.

[0023]

Embodiment 2

FIG. 3 illustrates an oblique perspective view of a multi-wavelength semiconductor laser device in Embodiment 2 of the invention, and FIG. 4 illustrates its plan view. The multi-wavelength semiconductor laser device includes a two-wavelength laser diode as one of the plurality of laser diodes.

[0024]

The multi-wavelength semiconductor laser device according to this embodiment includes a stem 101 that is formed from a metal plate into a discoid shape; a cylindrical block 103 whose bottom face is placed on the top face of the stem 101; two laser diodes 111 that are placed on the top face of the stem 101; two laser diodes 111 that are mounted on two side faces 209 of a "V"-shaped cross-section groove 205 formed laterally in the block 103; lead pins 113 that penetrate the stem 101; bonding wires 115 that connect the laser diodes 111 with the lead pins 113, respectively; and a ground pin 117 that is joined to the stem 101.

[0025]

The block 103 is formed of a metal material having high thermal conductivity, such as a copper alloy, and the groove 105 formed laterally in the block 103 coincides in direction with resonant directions of the laser diodes 111 mounted on the two side faces 209. The groove 205 in Embodiment 2 has a "V" cross-sectional shape that expands toward its opening, thereby more facilitating die bonding and wire bonding of the laser diodes 111.

[0026]

The two laser diodes 111 are soldered respectively to the two side faces 209 of the groove 205 formed in the block 103. Additionally, the laser diodes 111 may be mounted, as with Embodiment 1, on these faces 209 with submounts interposed therebetween. The laser diodes 111 are aligned so that their laser beams emit in parallel to the direction of the groove 205. One of the two laser diodes 111 is a two-wavelength laser diode that is capable of emitting laser beams having wavelengths of a 780 nm band (infrared) and a 650 nm band (red), and the other one is a blue-violet laser diode that has an emission wavelength of a 405 nm band (blue-violet). No restriction is imposed on their mounting order.

[0027]

The lead pins 113 are penetrated through the stem 101 with insulators each interposed therebetween and arranged near the respective laser diodes 111 mounted on the groove 205 of the block 103. Electrical connections are respectively made by the bonding wires 115 across the lead pins 113 and the p-side electrodes of the laser diodes 111.

[0028]

The ground pin 117 is welded to the stem 101 and electrically connected to the n-side electrodes (not shown) of the laser diodes 111 through the stem 101 and the block 103.

[0029]

With the multi-wavelength semiconductor laser device thus configured, since the two laser diodes 111 are soldered to the block 103 directly or with submounts interposed therebetween, heat generated during operation of the laser diodes 111 can efficiently dissipate externally through the block 103.

[0030]

Moreover, since the lead pins 113 are arranged near the respective laser diodes 111 mounted on the groove 205 of the block 103, wire bonding is facilitated across the lead pins 113 and the laser diodes 111, making easier the assembly process of the multi-wavelength semiconductor laser device compared to prior

arts and thus reducing its manufacturing costs.

[0031]

In particular, since the groove 205 formed in the block 103 has a "V" cross-sectional shape expanding toward its opening, it is possible to more easily perform die bonding and wire bonding of the laser diodes 111.

[0032]

Moreover, while the block 103 in Embodiment 2 has a cylindrical shape with the groove 205 formed therein, the present invention is not limited to such a shape but may employ a block, as with Embodiment 1, that has a cross section of a polygonal prism shape with such a groove formed therein.

[0033]

Furthermore, any of connecting locations of the three bonding wires 115 with the lead pins 113 and the lengths of the lead pins 113 may be altered individually as appropriate. These alterations allow more facilitating the wire bonding.

[0034]

According to Embodiment 2, a multi-wavelength semiconductor laser device includes a block 103 and laser diodes 111 whose emission wavelengths are different from each other, wherein the

block 103 has a "V"-shaped cross-section groove 205 formed therein in a predetermined direction with two side faces 209, and the laser diodes 111 are mounted on both side faces 209 so that their laser beams emit in the predetermined direction. Therefore, a multi-wavelength semiconductor laser device can be realized that has closely arranged emission points of the laser diodes 111, and is easy in optical design and excellent in heat dissipation, as well as being easily manufactured.

[0035]

Embodiment 3

FIG. 5 illustrates a plan view of a multi-wavelength semiconductor laser device in another embodiment of the invention. The multi-wavelength semiconductor laser device of Embodiment 3 includes a stem 101 that is formed from a metal plate into a discoid shape; a block 103 that has a rectangular projection 301 and whose bottom face is placed on the top face of the stem 101; and three laser diodes 111 that are mounted on a top face 303 and side faces 305 of the projection 301. Other configuration is the same as Embodiment 1.

[0036]

The laser diodes 111, mounted on the top face 303 and the side faces 305 of the projection 301, are aligned so that their laser beams emit in the same direction. Additionally, the laser diodes

111 may be mounted, as with Embodiment 1, on these faces with submounts interposed therebetween.

[0037]

With the multi-wavelength semiconductor laser device thus configured, since the three laser diodes 111 are soldered to the projection 301 directly or with submounts interposed therebetween, heat generated during operation of the laser diodes 111 can efficiently dissipate externally through the block 103.

[0038]

According to Embodiment 3, a multi-wavelength semiconductor laser device includes a block 103 and laser diodes 111 whose emission wavelengths are different from each other, wherein the block 103 is formed having a rectangular projection 301, and the laser diodes 111 are mounted on the top face 303 and side faces 305 of the projection 301. Therefore, a multi-wavelength semiconductor laser device can be realized that has closely arranged emission points of the laser diodes 111, and is easy in optical design and excellent in heat dissipation, as well as being easily manufactured. Accordingly, such a multi-wavelength semiconductor laser device can also exhibit the same effect as Embodiment 1.

[0039]

Embodiment 4

FIG. 6 illustrates a plan view of a multi-wavelength semiconductor laser device in still another embodiment of the invention. The multi-wavelength semiconductor laser device of Embodiment 4 includes a stem 101 that is formed from a metal plate into a discoid shape; a block 103 whose bottom face is placed on the top face of the stem 101; and three laser diodes 111 that are mounted on a flat face 401 of the block 103 and side faces 405 of a projection 403 extending from the flat face 401. Other configuration is the same as Embodiment 1.

[0040]

The laser diodes 111, mounted on the flat face 401 of the block 103 and the side faces 405 of the projection 403, are aligned so that their laser beams emit in the same direction. Additionally, the laser diodes 111 may be mounted, as with Embodiment 1, on these faces with submounts interposed therebetween.

[0041]

With the multi-wavelength semiconductor laser device thus configured, since the three laser diodes 111 are soldered to the flat face 401 of the block 103 and the side faces 405 of the projection 403 directly or with submounts interposed therebetween, heat generated during operation of the laser diodes 111 can efficiently dissipate externally through the block 103.

[0042]

According to Embodiment 4, a multi-wavelength semiconductor laser device includes a block 103 and laser diodes 111 whose emission wavelengths are different from each other, wherein the block 103 is formed having a flat face 401 and a projection 403 extending therefrom, and the laser diodes 111 are mounted on the flat face 401 and one of side faces 405 of the projection 403. Therefore, a multi-wavelength semiconductor laser device can be realized that has closely arranged emission points of the laser diodes 111, and is easier in optical design and excellent in heat dissipation, as well as being easily manufactured. Accordingly, such a multi-wavelength semiconductor laser device can also exhibit the same effect as Embodiment 1.

[0043]

Embodiment 5

FIG. 7 illustrates a plan view of a multi-wavelength semiconductor laser device in yet another embodiment of the invention. The multi-wavelength semiconductor laser device of Embodiment 5 includes a stem 101 that is formed from a metal plate into a discoid shape; a block 103 whose bottom face is placed on the top face of the stem 101; and three laser diodes 111 that are mounted on a flat face 401 of the block 103 and two side faces 405 of a projection 403 extending from the flat face 401. Other

configuration is the same as that of Embodiment 1.

[0044]

The laser diodes 111, mounted on the flat face 401 of the block 103 and the two side faces 405 of the projection 403, are aligned so that their laser beams emit in the same direction. Additionally, the laser diodes 111 may be mounted, as with Embodiment 1, on these faces with submounts interposed therebetween.

[0045]

With the multi-wavelength semiconductor laser device thus configured, since the three laser diodes 111 are soldered to the flat face 401 of the block 103 and the two side faces 405 of the projection 403 directly or with submounts interposed therebetween, heat generated during operation of the laser diodes 111 can efficiently dissipate externally through the block 103.

[0046]

According to Embodiment 5, a multi-wavelength semiconductor laser device includes a block 103 and laser diodes 111 whose emission wavelengths are different from each other, wherein the block 103 is formed having a flat face 401 and a projection 403 therefrom, and the laser diodes 111 are mounted on the flat face 401 and two side faces 405 of the projection 403. Therefore, a multi-wavelength semiconductor laser device can be realized that

has closely arranged emission points of the laser diodes 111, and is easier in optical design and excellent in heat dissipation, as well as being easily manufactured. Accordingly, such a multi-wavelength semiconductor laser device can also exhibit the same effect as Embodiment 1.

[0047]

Typical and preferable embodiments of the present invention have been disclosed in this specification and accompanying drawings. It should be noted that while specific terms are used in the specification, these terms are used only as general and descriptive meanings and not intended, as a matter of course, to limit the scopes of the claims set forth in the specification.

CLAIMS

What is claimed is:

1. A multi-wavelength semiconductor laser device comprising:
 - a block; and
 - two laser diodes whose emission wavelengths are different from each other, wherein
 - the block has a "V"-shape cross-section groove with two side faces, and
 - the laser diodes are mounted on both side faces of the groove so that the laser diodes emit their laser beams in the same direction.
2. The multi-wavelength semiconductor laser device of claim 1, wherein the block is installed on a stem.
3. A multi-wavelength semiconductor laser device comprising:
 - a block having a rectangular projection with three side faces; and
 - a plurality of laser diodes whose emission wavelengths are different from each other, wherein
 - the laser diode is mounted on each of the three side faces of the projection so that the laser diodes emit their laser beams in the same direction.
4. The multi-wavelength semiconductor laser device of claim 3, wherein the block is installed on a stem.
5. A multi-wavelength semiconductor laser device comprising:
 - a block having a projection with a first side face and a second side face; and
 - a plurality of laser diodes whose emission wavelengths are different from each other, wherein
 - the block is formed to have a first flat face intersecting the first side face and a second flat face intersecting the second side face; and
 - the laser diodes are mounted on two faces or more among the first side face, the second side face, the first flat face and the second flat face so

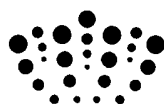
that the laser diodes emit their laser beams in the same direction.

6. The multi-wavelength semiconductor laser device of claim 5,
wherein the block is installed on a stem.

7. The multi-wavelength semiconductor laser device of claim 5, wherein two
of the laser diodes are mounted on the first flat face and the second flat face
of the block.

8. The multi-wavelength semiconductor laser device of claim 5, wherein two
of the laser diodes are mounted on the first side face and the second side face
of the projection.

9. The multi-wavelength semiconductor laser device according to any preceding claim and
substantially as herein before described with reference to the accompanying drawings.



Application No: GB1107789.8

Examiner: Claire Williams

Claims searched: 1 and 2

Date of search: 25 May 2011

Patents Act 1977: Search Report under Section 17

Documents considered to be relevant:

Category	Relevant to claims	Identity of document and passage or figure of particular relevance
Y	1, 2	EP0803949 A (CILAS) see also English description of equivalent US5930279 (in particular, Figure 2b and col 6 lines 1-14)
Y	1, 2	EP1038341 A (COHERENT) see Figure 6 and page 13
A	1	JP2002329893 A (KANSAI TLO KK) see Figure 6 and features 63 and abstract
A	1, 2	US5828683 A (FREITAS BARRY L) see abstract and Figure 1
A	1, 2	US2007/0116070 A (NLIGHT PHOTONICS) see Figures 6 and 7 and paragraphs 0039 and 0040

Categories:

X	Document indicating lack of novelty or inventive step	A	Document indicating technological background and/or state of the art.
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&	Member of the same patent family	E	Patent document published on or after, but with priority date earlier than, the filing date of this application.

Field of Search:

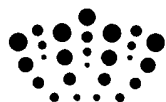
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International Classification:

Subclass	Subgroup	Valid From
H01S	0005/022	01/01/2006
H01L	0027/15	01/01/2006
H01L	0033/64	01/01/2010